



Bipolar PNP Bare Die – BTP6086

Part Description

The BTP6086 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = -60V
- VCEO = -60V
- VEBO = -5V
- hFE = 100-300 @ VCE = -10V, IC = -0.15A
- VCE(Sat) = -0.4V @ IC = -0.15A, IB = -15mA
- fT = 200 MHz @ VCE = -20V, IE = 0A
- COBO = 8pF @ VCB = -10V

Features

Low VCE(sat). Designed to provide performance equivalent to 2SA2166

Die Size (Unawn)

390µm X 390µm, 15 Mils X 15 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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